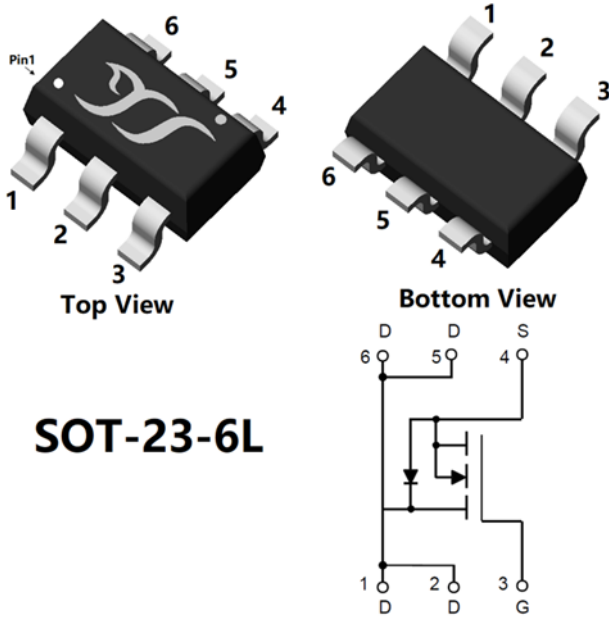


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	30V
• I_D	5.6A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	<22m Ω
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<26m Ω
• $R_{DS(ON)}$ (at $V_{GS}=2.5V$)	<42m Ω

General Description

- Trench Power MV MOSFET technology
- High Speed switching
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	30	V
Gate-source Voltage	V_{GS}	± 12	V
Drain Current	I_D	$T_A=25^\circ C$	5.6
		$T_A=100^\circ C$	3.5
Pulsed Drain Current ^A	I_{DM}	40	A
Total Power Dissipation ^B	P_D	$T_A=25^\circ C$	1.25
		$T_A=100^\circ C$	0.5
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^C	$R_{\theta JA}$	80	100	$^\circ C/W$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJJ3400B	F2	3400B	3000	30000	120000	7" reel



YJJ3400B

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
		V _{DS} =30V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	0.65	0.9	1.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.6A	-	17	22	mΩ
		V _{GS} =4.5V, I _D =3A	-	20	26	
		V _{GS} =2.5V, I _D =3A	-	28	42	
Diode Forward Voltage	V _{SD}	I _S =5.6A, V _{GS} =0V	-	-	1.2	V
Gate resistance	R _G	f=1MHz	-	3	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	5.6	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	610	-	pF
Output Capacitance	C _{oss}		-	60	-	
Reverse Transfer Capacitance	C _{rss}		-	50	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =5.6A	-	16	-	nC
Gate-Source Charge	Q _{gs}		-	2.4	-	
Gate-Drain Charge	Q _{gd}		-	2	-	
Reverse Recovery Charge	Q _{rr}	I _F =5.6A, di/dt=100A/us	-	4.5	-	nC
Reverse Recovery Time	t _{rr}		-	8.5	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =15V, I _D =5.6A R _{GEN} =3Ω	-	6	-	ns
Turn-on Rise Time	t _r		-	28	-	
Turn-off Delay Time	t _{D(off)}		-	16	-	
Turn-off fall Time	t _f		-	12	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case thermal resistance.

C. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



Typical Electrical and Thermal Characteristics Diagrams

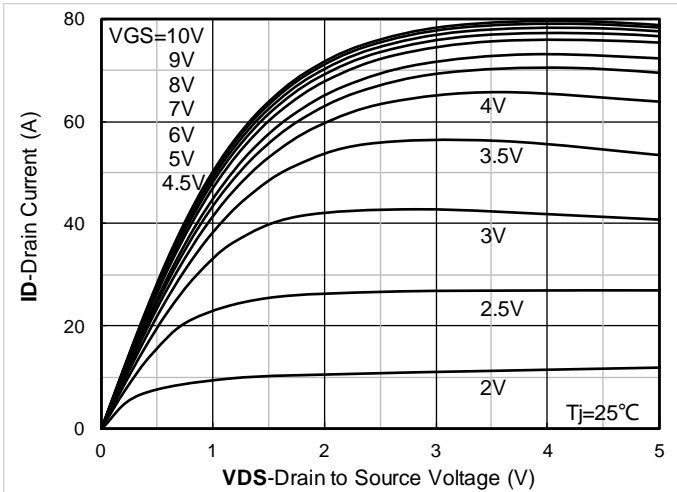


Figure 1. Output Characteristics

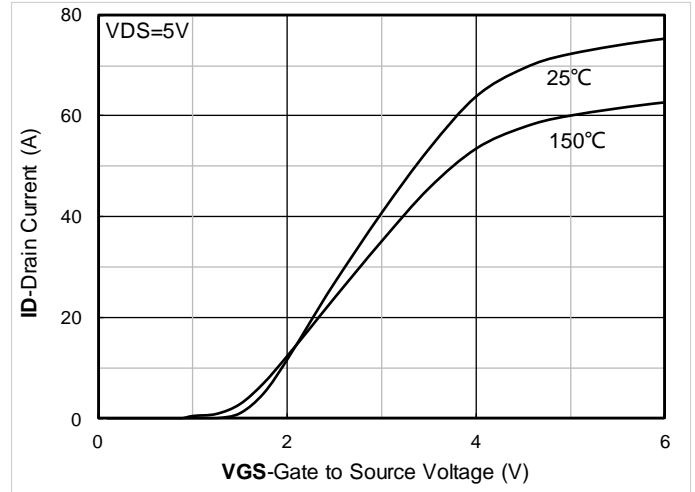


Figure 2. Transfer Characteristics

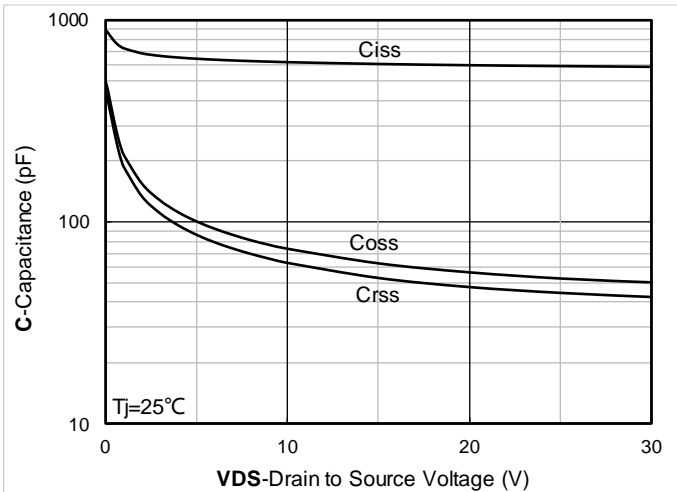


Figure 3. Capacitance Characteristics

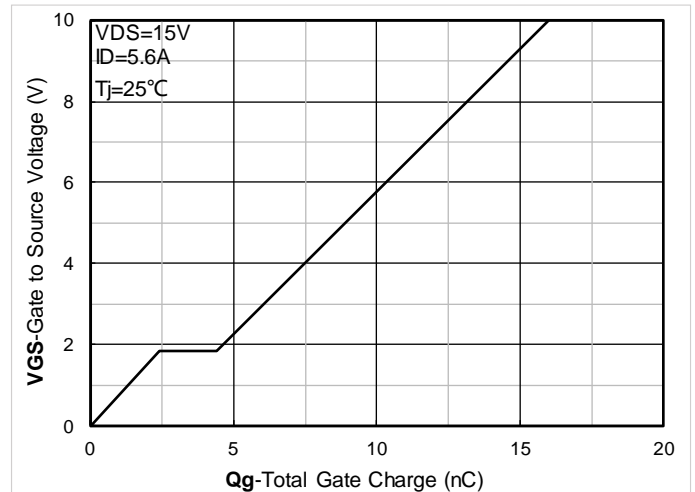


Figure 4. Gate Charge

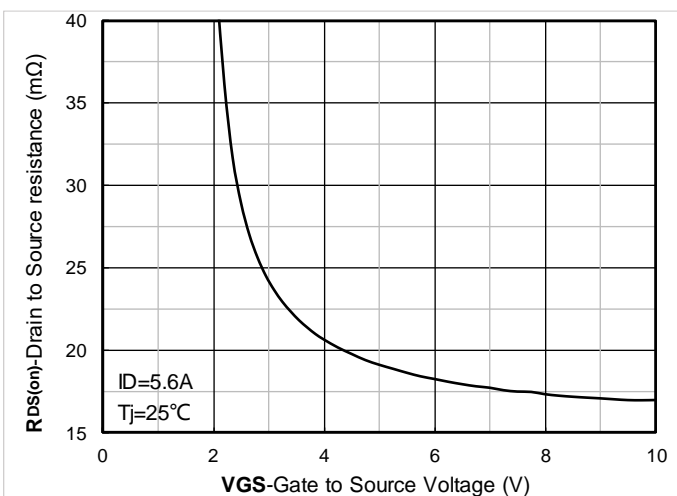


Figure 5. On-Resistance vs Gate to Source Voltage

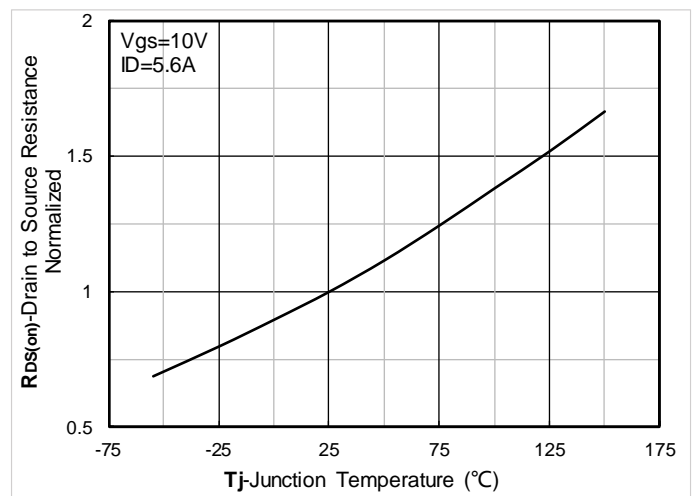


Figure 6. Normalized On-Resistance

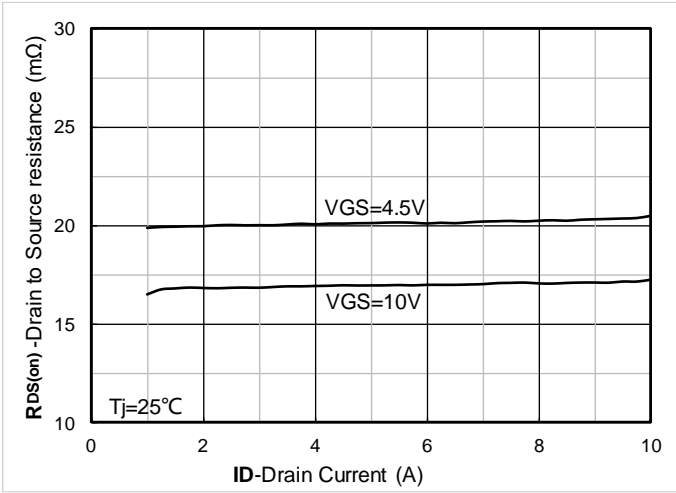


Figure 7. RDS(on) VS Drain Current

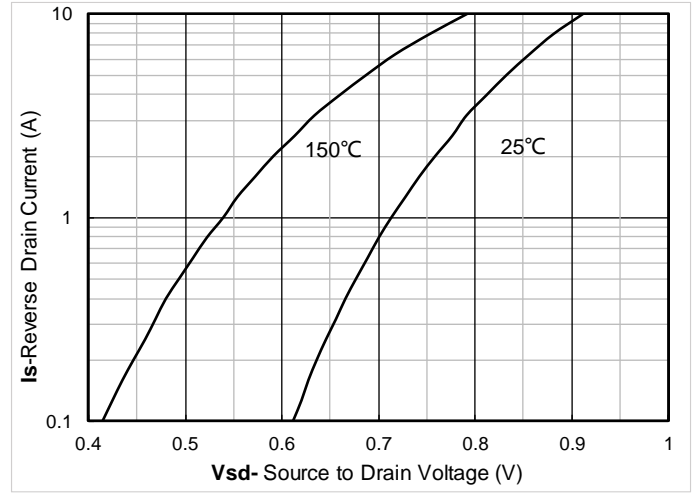


Figure 8. Forward characteristics of reverse diode

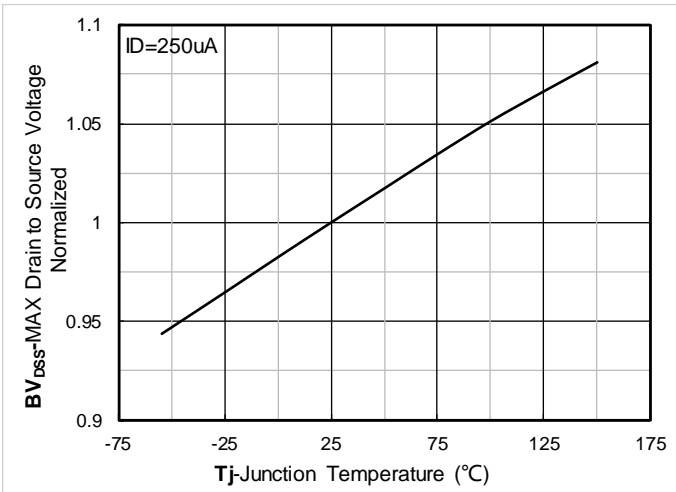


Figure 9. Normalized breakdown voltage

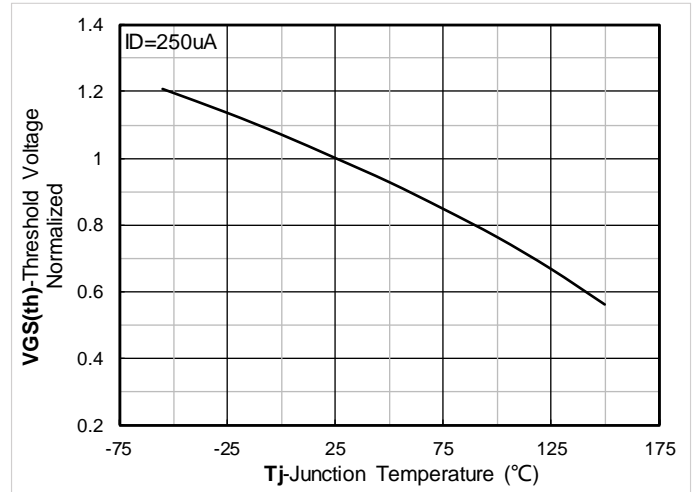


Figure 10. Normalized Threshold voltage

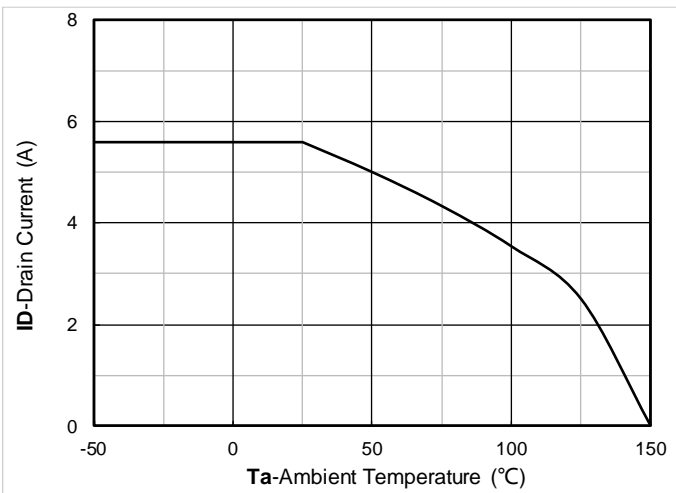


Figure 11. Current dissipation

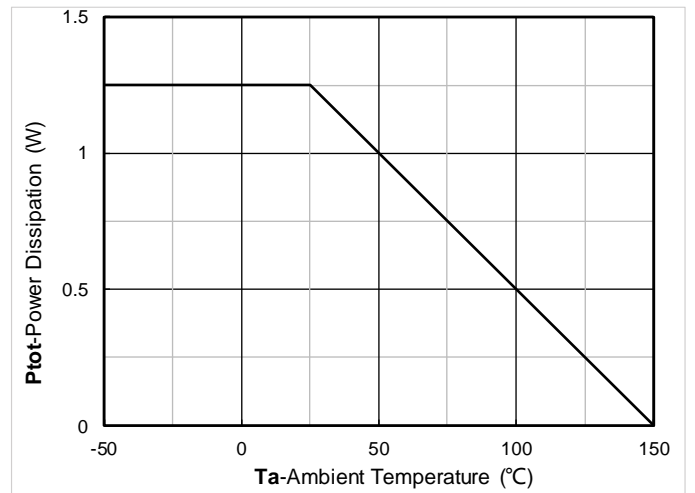


Figure 12. Power dissipation

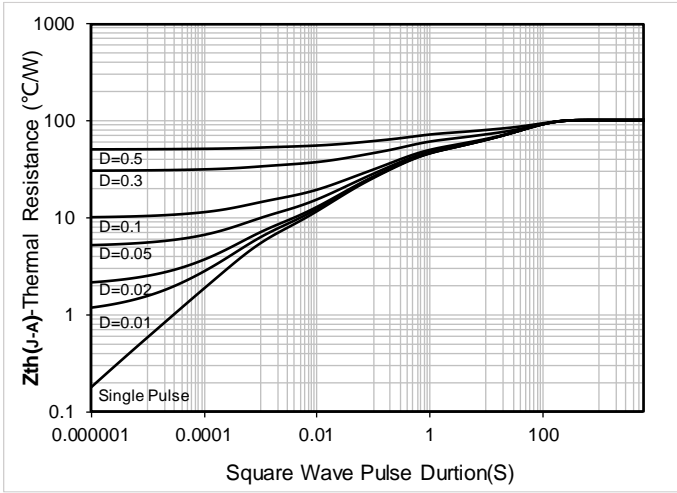


Figure 13. Maximum Transient Thermal Impedance

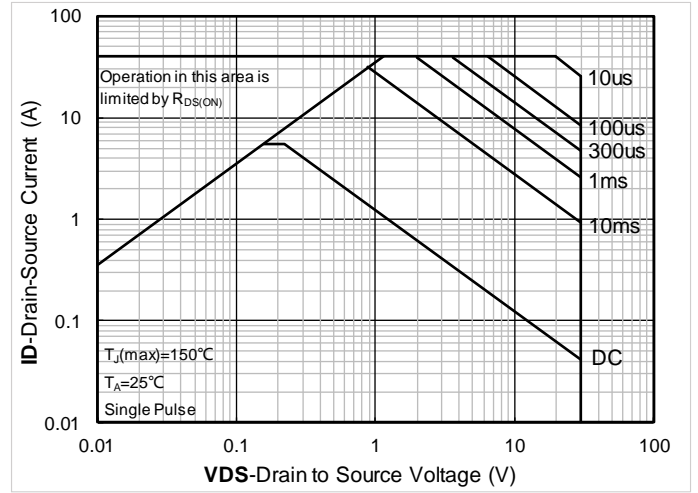


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

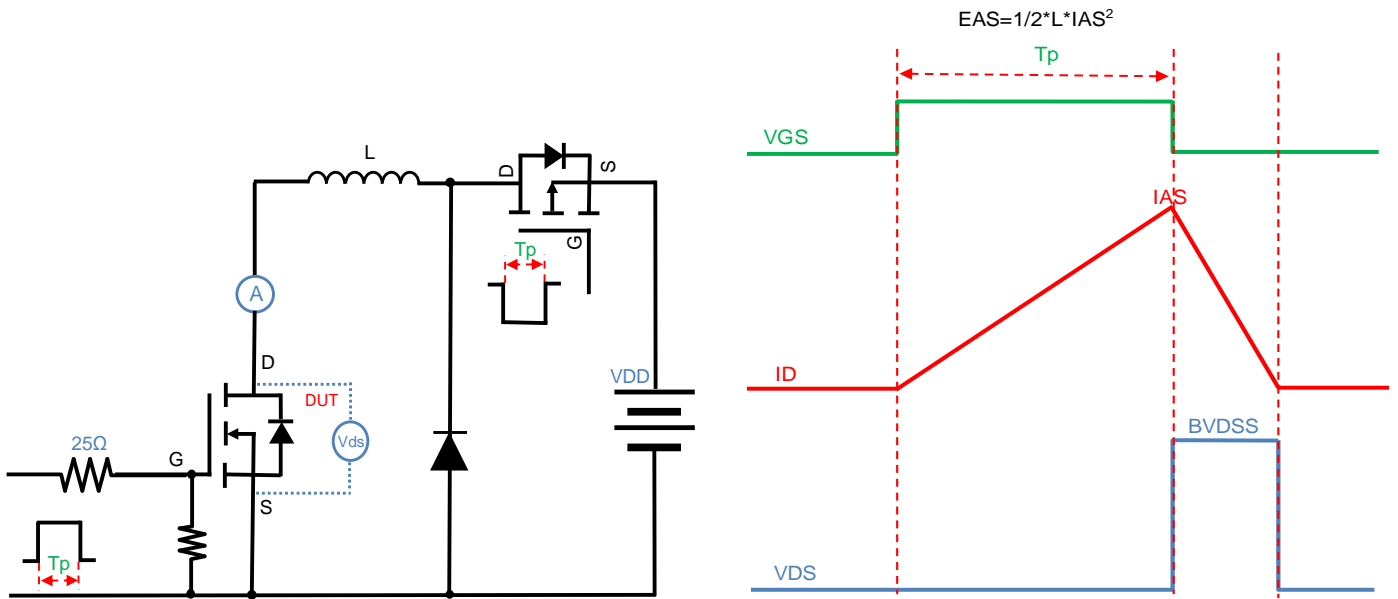


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

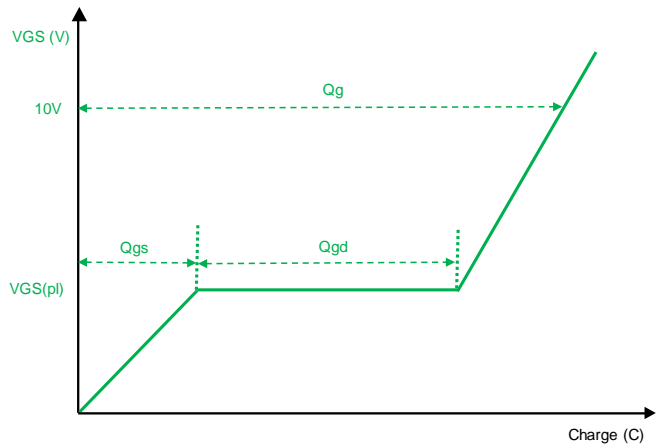


Figure B. Gate Charge Test Circuit & Waveform

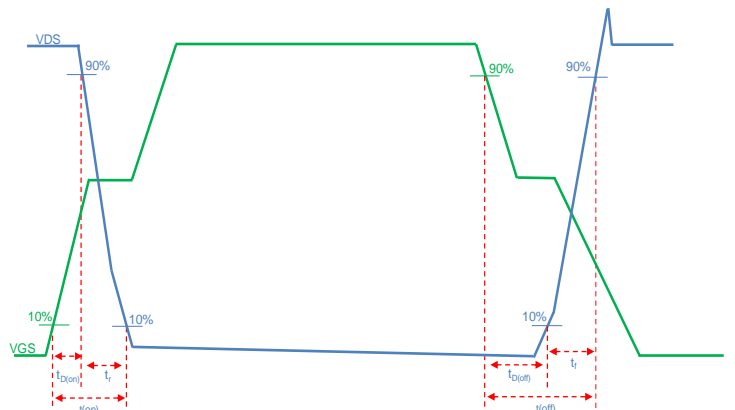
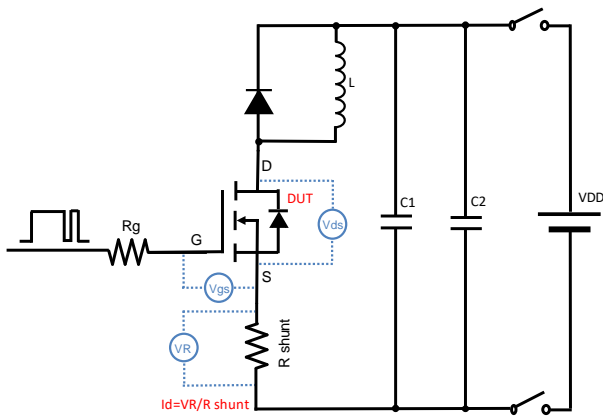


Figure C. Resistive Switching Test Circuit & Waveform

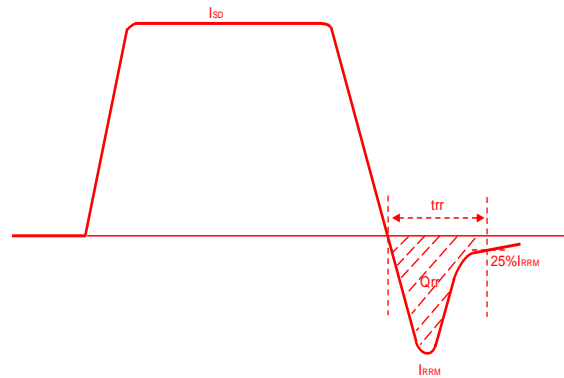
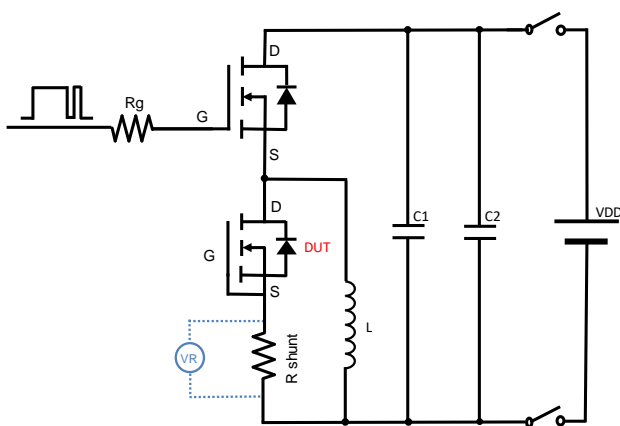
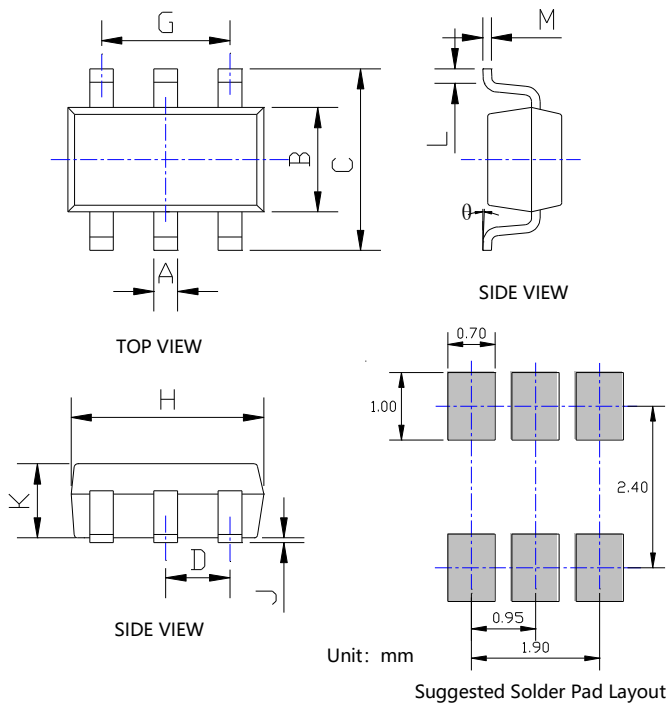


Figure D. Diode Recovery Test Circuit & Waveform

■ SOT-23-6L Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
θ	0°	8°	0°	8°

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.



YJJ3400B

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